

ABSTRACT OF THE DISCLOSURE

The present invention provides a channel region of a depletion
5 type lateral field effect transistor. The channel region of a first conductivity
type is selectively provided in a semiconductor region of a second
conductivity type, and the channel region underlies a gate insulating film,
wherein an interface of the channel region to the gate insulating film lies at
10 a lower level than an upper surface of the semiconductor region.